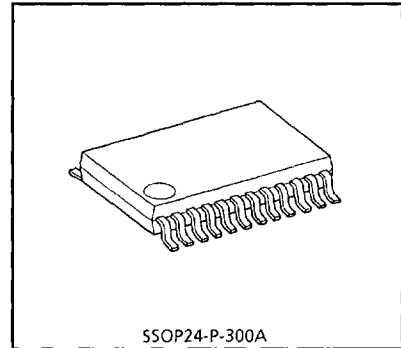


IF DETECT ICs

FM IF DETECTION IC FOR CORDLESS AND CELLULAR PHONES.

FEATURES

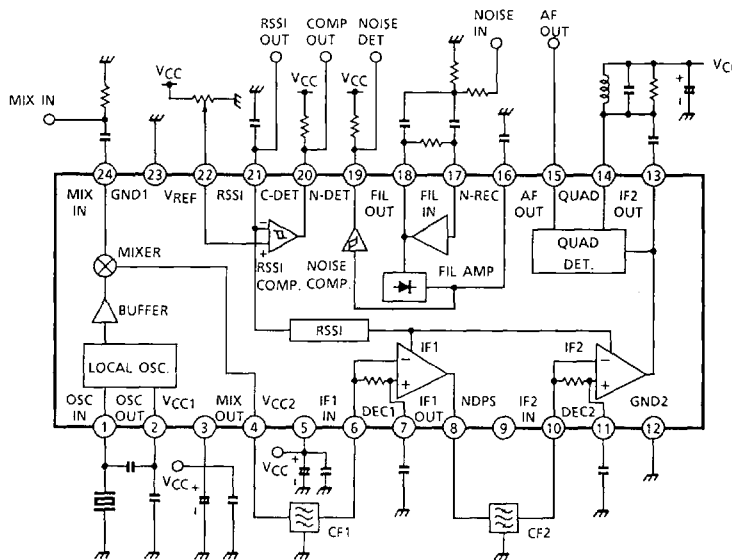
- Low operating voltage : $V_{CC} = 1.8 \sim 6.0V$
- Excellent temperature characteristic
- High selectivity can be designed by 2 IF Amps
- High sensitivity
12dB sensitivity : $8.5dB\mu V$ EMF (50Ω)
- Intercept point is very high : $107dB\mu V$ (0dBm)
- Built-in 2nd MIXER
Operating frequency : $10 \sim 150MHz$
- Built-in noise detection circuit
- RSSI function
- RSSI comparator
- Small current consumption : $I_{CC} = 3.8mA$
- Small package (0.65mm pitch)



SSOP24-P-300A

Weight : 0.14g (Typ.)

BLOCK DIAGRAM



TA31137FN-1

IF DETECT ICs

PIN FUNCTION (The values of resistor and capacitor are typical.)

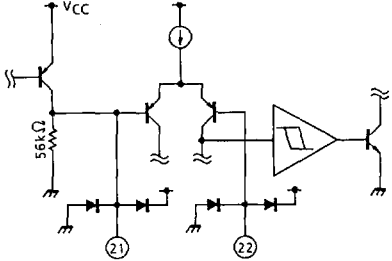
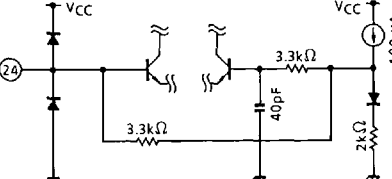
PIN No.	PIN NAME	FUNCTION	INTERNAL EQUIVALENT CIRCUIT
1	OSC IN	Local oscillator input and output terminals. Colpitts Oscillator is formed by internal emitter follower and external X'tal. And external injection is possible from pin 2.	
2	OSC OUT		
3	V _{CC1}	Power supply 1	—
4	MIX OUT	MIX Output terminal. Output impedance is around 1.8kΩ.	
5	V _{CC2}	Power supply 2	—
6	IF1 IN	IF1 input and decoupling for bias. Input impedance is around 1.8kΩ.	
7	DEC1		
8	IF1 OUT	Output terminal of IF1 AMP.	
9	NDPS	Connect to V _{CC}	—
10	IF2 IN	IF2 input and decoupling for bias. Input impedance is around 1.8kΩ.	
11	DEC2		
12	GND2	GND terminal	—
13	IF2 OUT	Output terminal of IF2 AMP.	

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IF DETECT ICs

PIN No.	PIN NAME	FUNCTION	INTERNAL EQUIVALENT CIRCUIT
14	QUAD	Phase input terminal of FM demodulator.	
15	AF OUT	Demodulate signal output terminal. Carrier leak is small as LPF is built-in. Output impedance is around 360Ω.	
16	N-REC	After output of inverter AMP. amplified around 20dB, noise signal is rectified by external capacitor.	
17	FIL IN	Inverter AMP. input and output terminal. BPF is composed of external capacitors and resistors.	
18	FIL OUT	Connected internally to rectifier circuit by coupling capacitor.	
19	N-DET	The result of noise detection is output by comparing output voltage of N-REC terminal with internal reference. Hysteresis range is about 100mV and output is open collector.	
20	C-DET	Comparison output terminal of VREF terminal input voltage and RSSI terminal output voltage. When VREF < RSSI, C-DET output is "L" level.	

IF DETECT ICs

PIN No.	PIN NAME	FUNCTION	INTERNAL EQUIVALENT CIRCUIT
21	RSSI	This terminal outputs DC level according to input signal level to IF AMP. Dynamic range is around 70dB.	
22	VREF	Reference voltage input terminal.	
23	GND1	GND terminal	—
24	MIX IN	1st IF signal input terminal.	

TA31137FN-4

1. Local oscillator external injection method

Inject as shown in Figure 1. Setting the injection level between $95\text{dB}\mu\text{V}$ and $100\text{dB}\mu\text{V}$. A built-in buffer AMP. minimizes leakage from the MIX.

Input from pin 1 is possible as shown in Figure 2. However, when the input frequency is high, the level at pin 2 may not be sufficient, causing a decrease in sensitivity. In such a case, add resistor R_{51} and set the input signal so that signal level at pin 2 is adequate. The input capacitance of pins 1 and 2 are respectively 2.4pF (Typ.) and 4.5pF (Typ.).

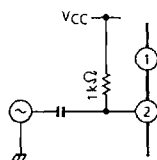


Figure 1

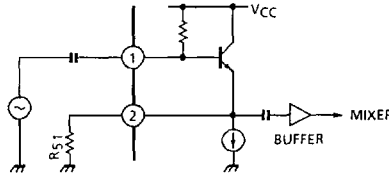


Figure 2

2. Overtone oscillation

Figure 3 shows the basic configuration of the local oscillation circuit using overtone oscillation. The C_{51} and L_1 tuning circuits prevent crystal fundamental oscillation. Therefore, set C_{51} and L_1 to inductive at the fundamental frequency and capacitive at the overtone frequency. Since the level at pin 2 may decrease and the sensitivity may fall at high frequency as with external injection, adjust the oscillation level using R_{51} .

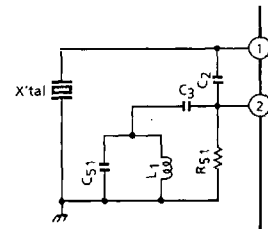


Figure 3

3. Detection circuit

Demodulation output can be increased by raising damping resistance R_3 . However, be careful because the temperature dependency of the modulation output also increases. The demodulation output depends largely on C_{101} . For C_{101} , use a capacitor with good temperature characteristics.

4. NDPS terminal

The NDPS terminal (pin 9) is used for the power source for the 16-19 pin block. When pins 16-19 are not in use, current consumption can be reduced by opening the NDPS terminal. (In this case, pins 16-19 can be open.)

5. C-DET terminal

The C-DET terminal (pin 20) is used for the comparator output of the VREF terminal (pin 22) output voltage and the RSSI terminal (pin 21) output voltage.

When $V_{REF} > RSSI$, C-DET = high level

When $V_{REF} < RSSI$, C-DET = low level

* The hysteresis range is about 30V (Typ.).

When not in use, set pin 20 to open and connect pin 22 to V_{CC} .

IF DETECT ICs

6. Inverter AMP. usage

The inverter amp. can be used to form a band pass filter as shown in Figure 4.

Set constants as in equations (1) to (3). However, because a low pass filter and a high pass filter are built in, it is recommended that center frequency f_0 be about 30kHz.

$$(1) \quad f_0 = \frac{1}{2\pi\sqrt{R_4(R_5 // R_6)C^2}}$$

$$(2) \quad G_V = R_4 / 2 \times R_5$$

$$(3) \quad Q^2 = \frac{R_4}{4(R_5 // R_6)}$$

at $R_5 \gg R_p$

Example: $R_4 = 150k\Omega$, $R_5 = 330k\Omega$

$R_6 = 3.3k\Omega$, $R_p = 20k\Omega$ (VR)

When $C = 220pF$

$f_0 \approx 31kHz$, $G_V \approx -13dB$

$Q^2 \approx 12$

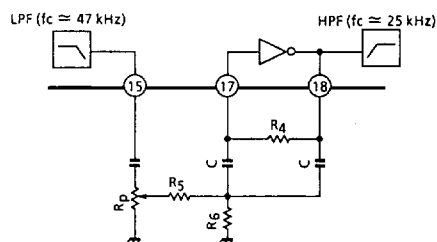


Figure 4

7. Noise detect rise time

The rise time is a proportion of time constant 7.5ms of the smoothing capacitor $C_g = 0.1\mu F$ of the noise rectifier and internal resistor $75k\Omega$. Although decreasing the capacitance of C_g can shorten the rise time, note that the noise detection output fluctuation may increase. This should be taken into account before use.

8. RSSI function

A DC voltage corresponding to the input level of IF input pins (pin 6 and pin 10) is output to the RSSI pin (pin 21). While the linear range is about 70dB when $V_{CC}=2V$, the range can be expanded to 80dB as in Figure 5.

However, in such a case, note that the temperature characteristics of the RSSI output may alter due to a disparity between the temperature coefficient of the external resistor and the internal resistance of the IC.

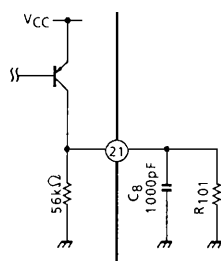
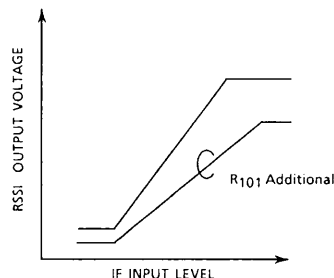


Figure 5



9. DC voltages for pins (Typical values for reference)

$V_{CC}=3.0V$

PIN No.	PIN NAME	VOLTAGE	PIN No.	PIN NAME	VOLTAGE
1	OCS IN	2.98	13	IF2 OUT	2.14
2	OSC OUT	2.28	14	QUAD	3.0
3	V_{CC1}	3.0	15	AF OUT	—
4	MIX OUT	1.76	16	N-REC	—
5	V_{CC2}	3.0	17	FIL IN	0.64
6	IF1 IN	2.58	18	FIL OUT	0.66
7	DEC 1	2.58	19	N-DET	—
8	IF1 OUT	2.0	20	C-DET	—
9	NDPS	3.0	21	RSSI	—
10	IF2 IN	2.65	22	V_{REF}	—
11	DEC 2	2.65	23	GND 1	0.0
12	GND 2	0.0	24	MIX IN	0.93

(Unit : V)

IF DETECT ICs

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{CC}	7	V
Power Dissipation	P _D	780	mW
Operating Temperature	T _{opr}	-30~85	°C
Storage Temperature	T _{stg}	-50~150	°C

ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, V_{CC} = 3.0V, f_{IN} (MIX) = 80.455MHz, Δf = ±8.0kHz, f_{mod} = 1kHz, Ta = 25°C, f_{IN} (osc) = 80MHz, V_{IN} (osc) = 100dBμV, f_{IN} (IF) = 455kHz, V_{IN} (IF) = 60dBμV.)

CHARACTERISTIC	SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{CC}	—		1.8	3.0	6.0	V
Quiescent Current	I _{CCQ}	—	With NOISE CIRCUIT	—	4.1	5.6	mA
	I _{CCQN}	—	Without NOISE CIRCUIT	—	3.8	5.2	mA
Mixer Conversion Gain	G _{VC}	—	Measurement after ceramic filter	12.5	15.5	18.5	dB
Mixer Intercept Point	P _{IM}	—		—	107	—	dBμV
Mixer Input Impedance	R _{IN} (MIX)	—		—	4.5	—	kΩ
	C _{IN} (MIX)	—		—	2.4	—	pF
Mixer Output Resistance	R _{OUT} (MIX)	—		1.2	1.8	2.4	kΩ
12dB Sensitivity	12dB S/N	—	50Ω Input	—	8.5	—	dBμV EMF
Demodulated Output	V _{OD}	—	V _{IN} (IF) = 60dBμV EMF	160	210	280	mV _{rms}
S/N Ratio	S/N	—	V _{IN} (IF) = 60dBμV EMF	50	65	—	dB
AM Rejection Ratio	AMR	—	V _{IN} (IF) = 60dBμV EMF, AM = 30%	—	48	—	dB
IF1 Gain	G (IF1)	—		—	25	—	dB
IF2 Gain	G (IF2)	—		—	77	—	dB
IF1 Input Resistance	R _{IN} (IF1)	—		1.2	1.8	2.4	kΩ
IF1 Output Resistance	R _{OUT} (IF1)	—		1.2	1.8	2.4	kΩ
IF2 Input Resistance	R _{IN} (IF2)	—		1.2	1.8	2.4	kΩ
AF Output Impedance	Z _{AF}	—		—	360	—	Ω
RSSI Output Voltage	V _{RSSI-1}	—	V _{CC} = 3V, V _{IN} (IF) = 20dBμV EMF	0.1	0.25	0.45	V
	V _{RSSI-2}	—	V _{CC} = 3V, V _{IN} (IF) = 100dBμV EMF	1.8	2.2	2.6	V

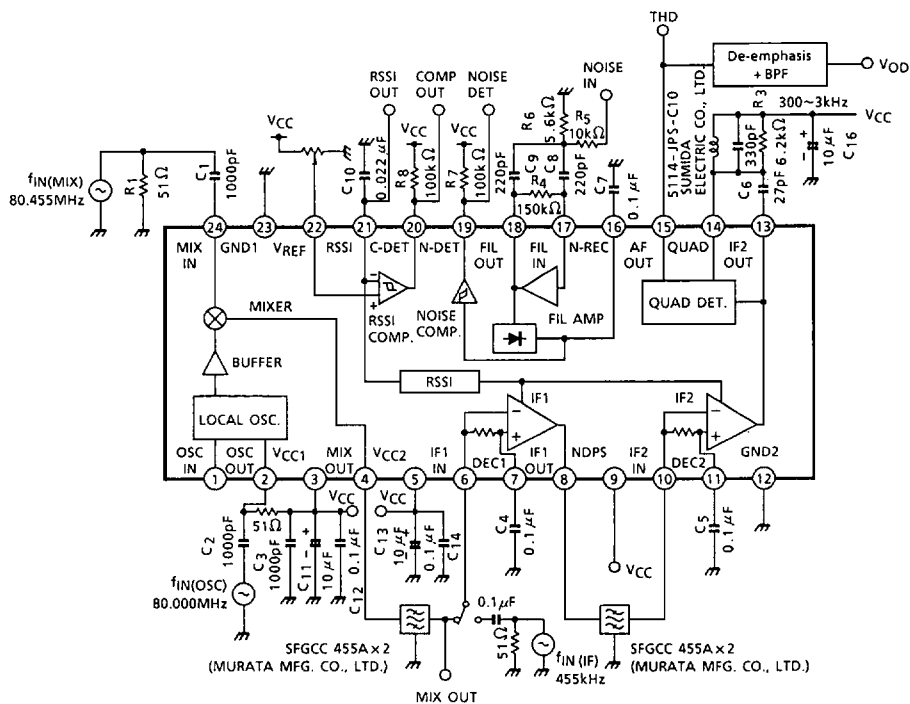
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IF DETECT ICs

CHARACTERISTIC	SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Noise Detection Output Voltage	V_{NDET}	—	$I_{SINK} = 0.2mA$	—	0.1	0.5	V
Noise Detection Out Leak Current	I_{LEAK}	—	$V_{NREC} = 0.6V, V_{NDET} = 2V$	—	0	5	μA
Noise Detection "H" Level	V_{TH-H}	—		—	0.5	0.7	V
Noise Detection "L" Level	V_{TH-L}	—		0.3	0.4	—	V
RSSI Comparator Range Of Hysteresis	V_{HYS}	—		—	30	—	mV
RSSI Comparator Input Range Of Reference	ΔV_{REF}	—		0.3	—	$V_{CC} - 1$	V

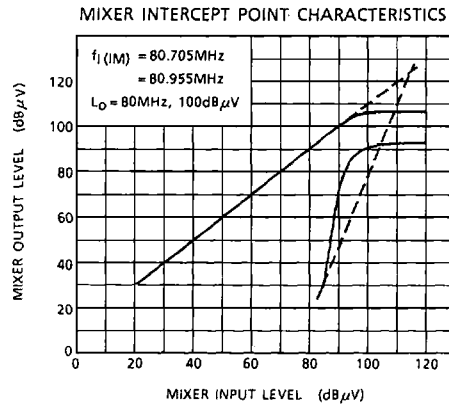
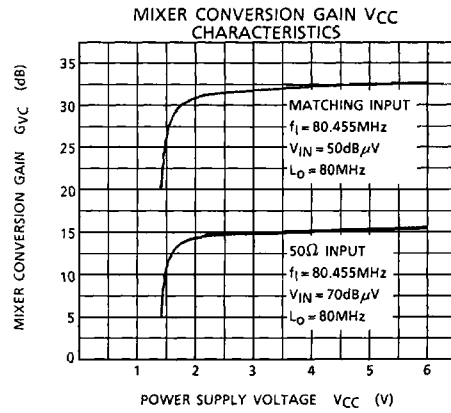
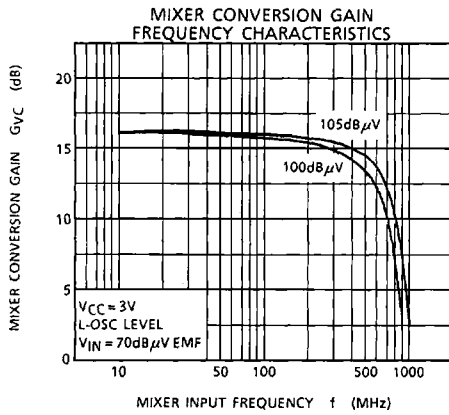
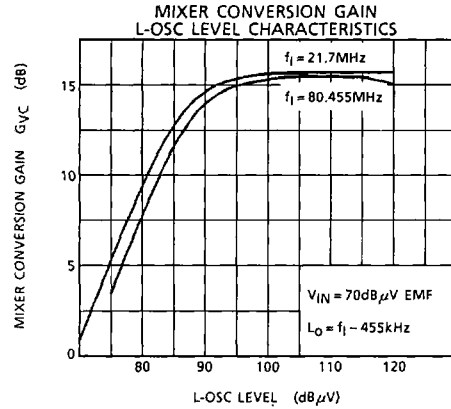
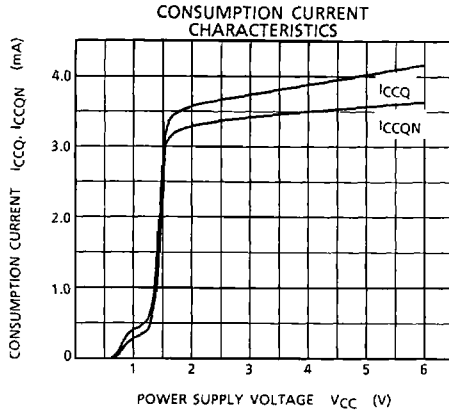
IF DETECT ICs

TEST CIRCUIT

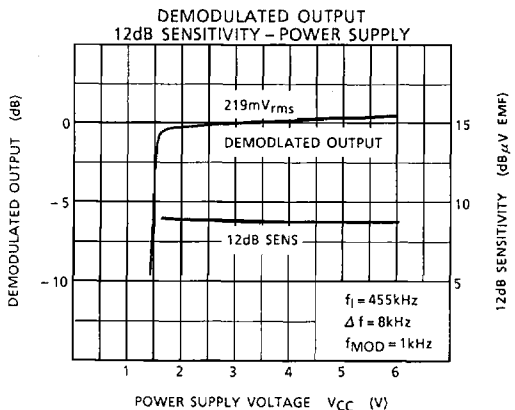
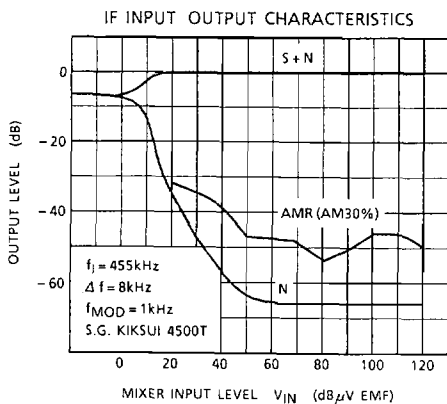
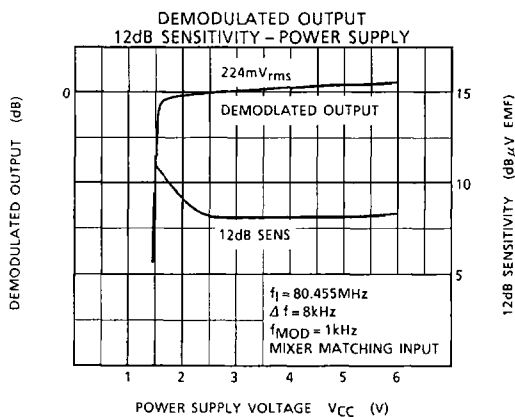
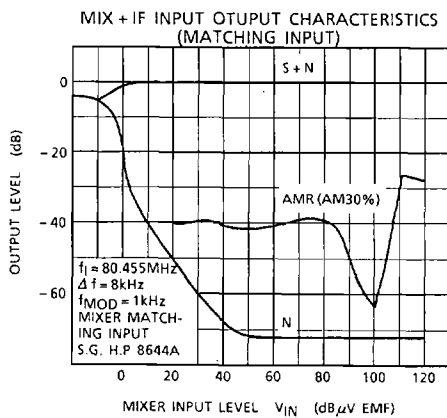
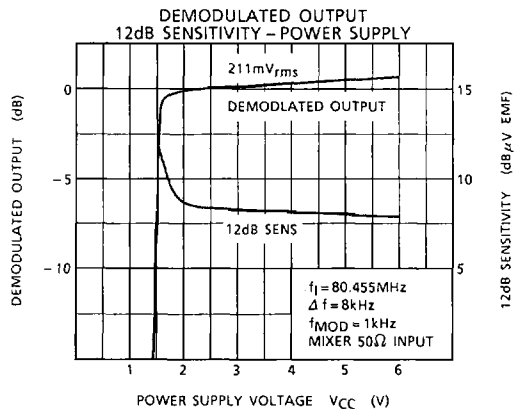
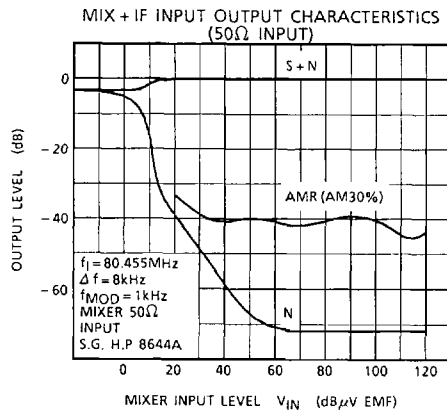


TA31137FN-10

IF DETECT ICs



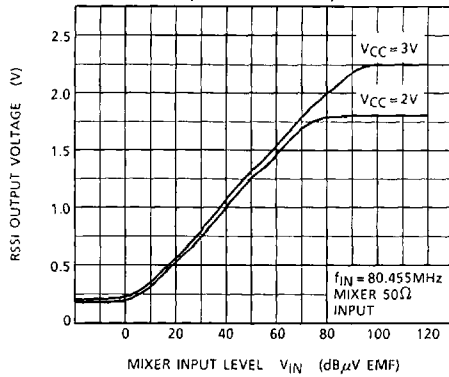
IF DETECT ICs



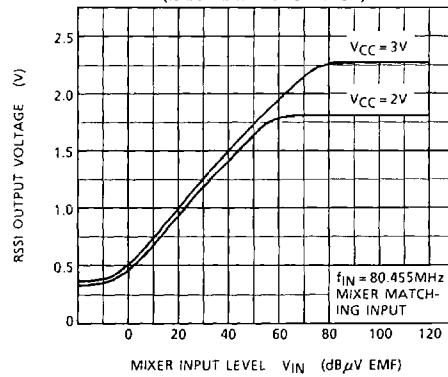
TA31137FN-12

IF DETECT ICs

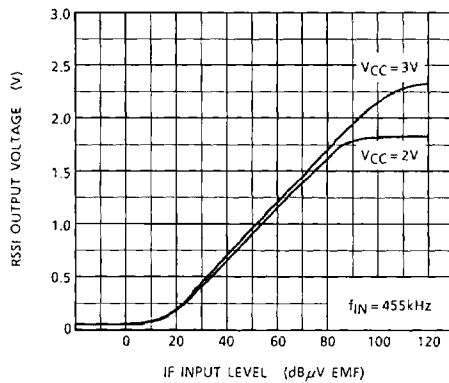
MIX + IF RSSI INPUT OUTPUT CHARACTERISTICS
(MIX 50Ω INPUT)



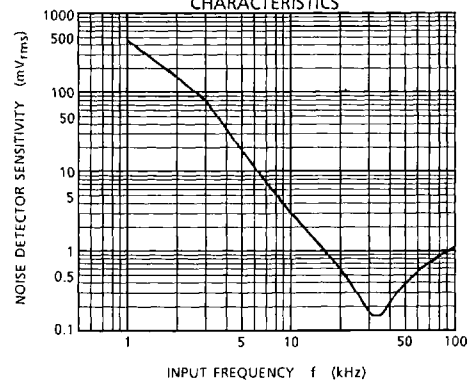
MIX + IF RSSI INPUT OUTPUT CHARACTERISTICS
(MIX MATCHING INPUT)



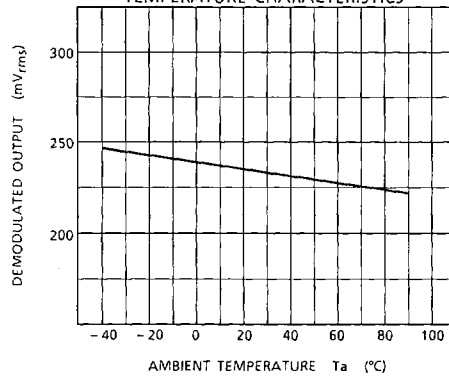
IF1 RSSI INPUT OUTPUT CHARACTERISTICS



NOISE DETECTION FREQUENCY CHARACTERISTICS



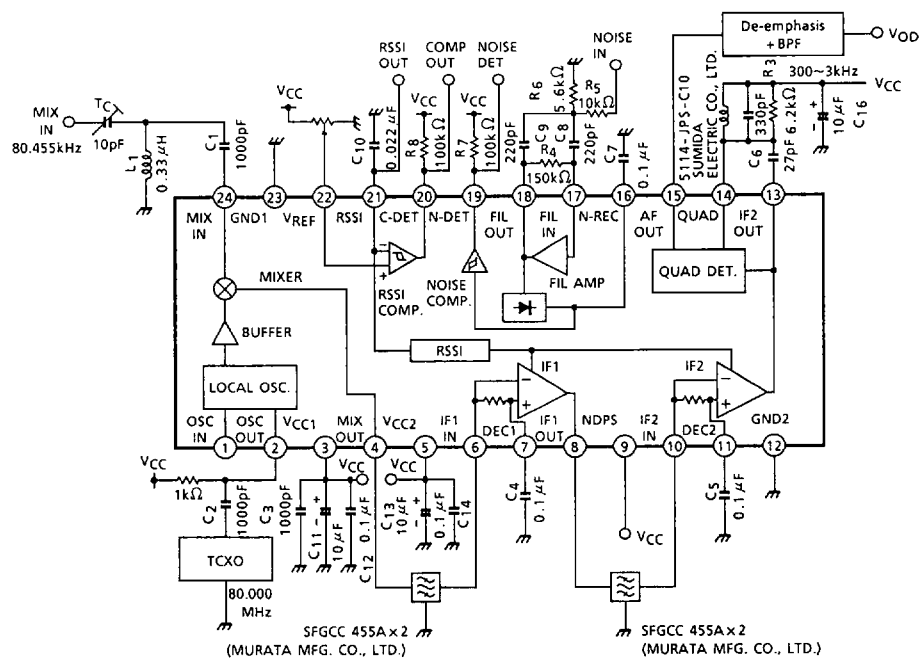
DEMODULATED OUTPUT TEMPERATURE CHARACTERISTICS



TA31137FN-13

IF DETECT ICs

APPLICATION CIRCUIT



TA31137FN-14